

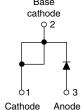
VS-MUR820PbF, VS-MUR820-N3

Vishay Semiconductors

Ultrafast Rectifier, 8 A FRED Pt®







CT SUMMARY		

PRODUCT SUMMARY					
Package	TO-220AC				
I _{F(AV)}	8 A				
V_{R}	200 V				
V _F at I _F	0.975 V				
t _{rr} typ.	See Recovery table				
T _J max.	175 °C				
Diode variation	Single die				

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)





ROHS COMPLIANT HALOGEN FREE

DESCRIPTION/APPLICATIONS

VS-MUR820PbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Peak repetitive reverse voltage	V_{RRM}		200	V				
Average rectified forward current	I _{F(AV)}	Total device, rated V _R , T _C = 150 °C	8					
Non-repetitive peak surge current	I _{FSM}		100	Α				
Peak repetitive forward current	I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 150 °C	16					
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS MIN. TYP. MAX				UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-		
Forward voltage V _F	V-	I _F = 8 A	-	-	0.975		
	٧F	I _F = 8 A, T _J = 150 °C	-	-	0.895		
Poverse leekage ourrent		$V_R = V_R$ rated	-	-	5		
Reverse leakage current	I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	-	250	μA	
Junction capacitance	C _T	V _R = 200 V	-	25	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)											
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS				
		$I_F = 1.0 \text{ A, } dI_F/dt =$	$50 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	i	-	35					
Reverse recovery time	t _{rr}	I _F = 0.5 A, I _R = 1.0 A, I _{REC} = 0.25 A		-	-	25	ns				
		T _J = 25 °C		-	20	-	115				
		T _J = 125 °C		-	34	-					
Dook roopyony ourront	_	T _J = 25 °C	$I_F = 8 A$	-	1.7	-	Α				
Peak recovery current	IRRM	IRRM	IRRM	IRRM	IRRM	T _J = 125 °C	dI _F /dt = 200 A/μs V _R = 160 V	-	4.2	-	A
Reverse recovery charge	0	T _J = 25 °C		-	23	-	nC				
	Q_{rr}	T _J = 125 °C			-	75	-	IIC			

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C		
Thermal resistance, junction to case	R _{thJC}		-	-	3.0			
Thermal resistance, junction to ambient	R _{thJA}		-	-	50	°C/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-			
Weight			-	2.0	-	g		
vveigni			-	0.07	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-220AC		MUF	R820	•		



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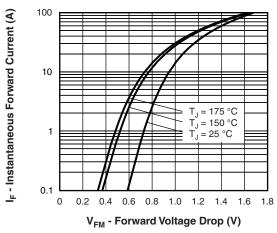


Fig. 1 - Maximum Forward Voltage Drop Characteristics

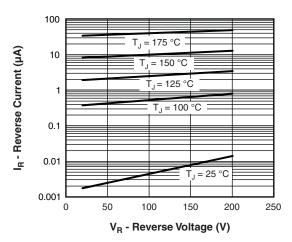


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

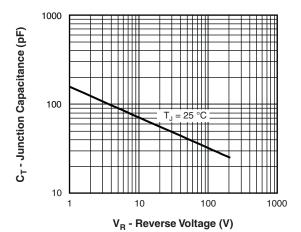


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

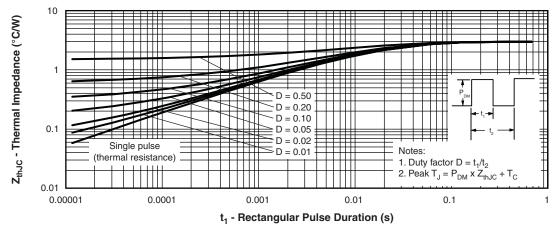


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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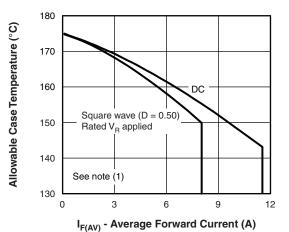
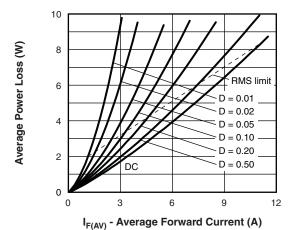


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current



Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = Inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = Rated V_R

Fig. 6 - Forward Power Loss Characteristics Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

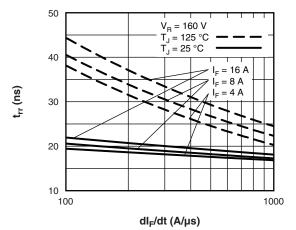


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

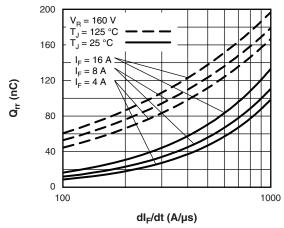


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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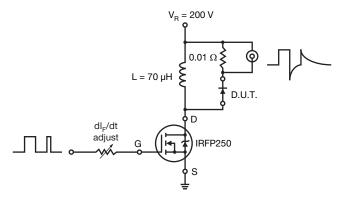
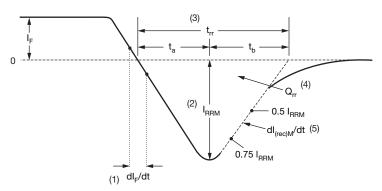


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

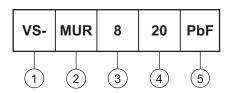
Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Ultrafast MUR series

3 - Current rating (8 = 8 A)

Voltage rating (20 = 200 V)

5 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-MUR820PbF	50	1000	Antistatic plastic tube				
VS-MUR820-N3	50	1000	Antistatic plastic tube				

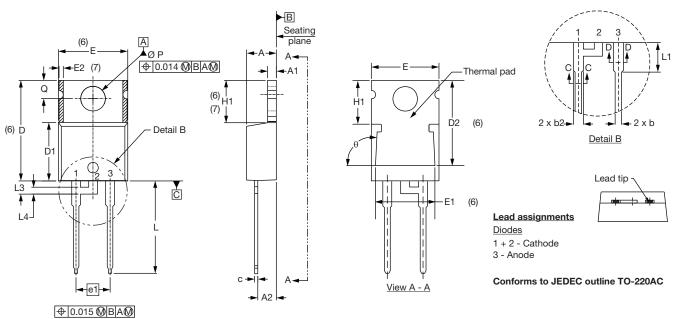
LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?95221</u>						
Deut annulium information	TO-220ACPbF	www.vishay.com/doc?95224				
Part marking information	TO-220AC-N3	www.vishay.com/doc?95068				



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TO-220AC

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	IETERS	INCHES		NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
Е	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIM	MILLIMETERS INCHES NOT		INCHES		
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
E1	6.86	8.89	0.270	0.350	6	
E2	-	0.76	-	0.030	7	
е	2.41	2.67	0.095	0.105		
e1	4.88	5.28	0.192	0.208		
H1	6.09	6.48	0.240	0.255	6, 7	
L	13.52	14.02	0.532	0.552		
L1	3.32	3.82	0.131	0.150	2	
L3	1.78	2.13	0.070	0.084		
L4	0.76	1.27	0.030	0.050	2	
ØΡ	3.54	3.73	0.139	0.147		
Q	2.60	3.00	0.102	0.118		
θ	90° t	o 93°	90° to 93°			

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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